

Vishay Siliconix

Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
- 20	0.031 at V _{GS} = - 4.5 V	- 4.8		
	0.041 at V _{GS} = - 2.5 V	- 4.2		
	0.058 at V _{GS} = - 1.8 V	- 3.5		

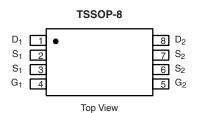
FEATURES

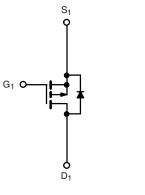
- Halogen-free
- TrenchFET[®] Power MOSFETs

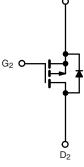
APPLICATIONS

- Load Switch
- Battery Switch









 S_2

Ordering Information: Si6981DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	_A = 25 °C, unle	ss otherwise r	oted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current /T 150 °C)	T _A = 25 °C	- I _D	- 4.8	- 4.1	٨	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 3.9	- 3.2		
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	- 30		A	
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 1.0 - 0.7			
Manimum Damar Diasia atiana	T _A = 25 °C	- P _D	1.14	0.83	W	
Maximum Power Dissipation ^a	T _A = 70 °C		0.73	0.53	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manimum langting to Angling 12	t ≤ 10 s	- R _{thJA} R _{thJF}	86	110	
Maximum Junction-to-Ambient ^a	Steady State		124	150	°C/W
Maximum Junction-to-Foot (Drain)	Steady State		59	75	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -300 \ \mu A$	- 0.40		- 0.9	V		
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V			± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	$\frac{V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}}{V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}}$				μA		
							On-State Drain Current ^a	I _{D(on)}
Drain-Source On-State Resistance ^a	R _{DS(on)}	V_{GS} = - 4.5 V, I _D = - 4.8 A		0.026	0.031	Ω		
		V _{GS} = - 2.5 V, I _D = - 4.2 A		0.034	0.041			
		V _{GS} = - 1.8 V, I _D = - 3.5 A		0.046	0.058			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 4.8 A		17		S		
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.65	- 1.1	V		
Dynamic ^b								
Total Gate Charge	Qg			15	25	nC		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 4.8 A		2.4				
Gate-Drain Charge	Q _{gd}			3.8		1		
Turn-On Delay Time	t _{d(on)}			35	55			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		55	85	ns		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_{\text{D}}\cong$ - 1 A, V_{GEN} = - 4.5 V, R_{G} = 6 Ω		120	180			
Fall Time	t _f			52	80			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.0 A, dl/dt = 100 A/μs		30	50			

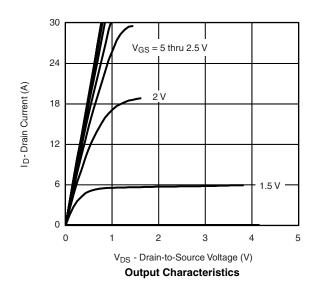
Notes:

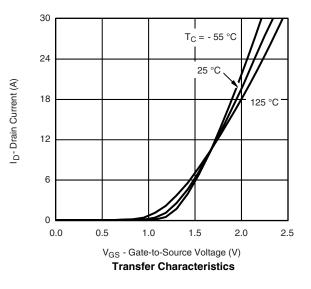
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



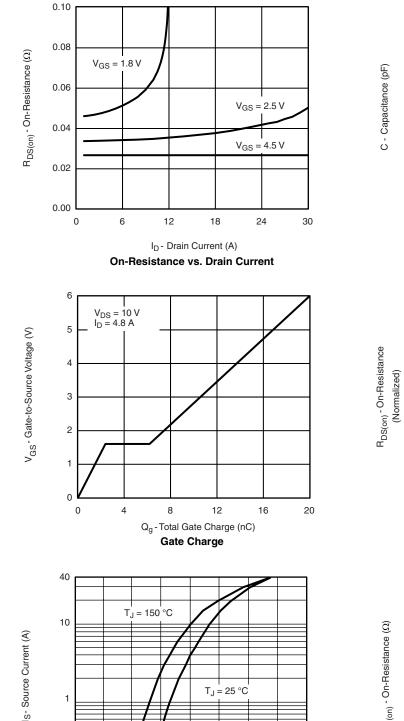


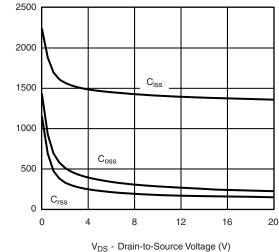


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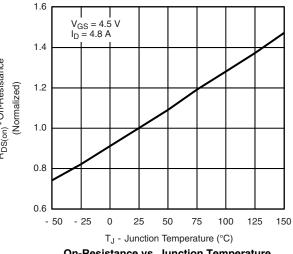
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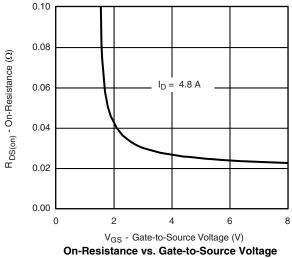




Capacitance



On-Resistance vs. Junction Temperature



Document Number: 72226 S-81221-Rev. B, 02-Jun-08

1

0.2 0.0

0.2

0.4

0.6

0.8

V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

1.0

1.2

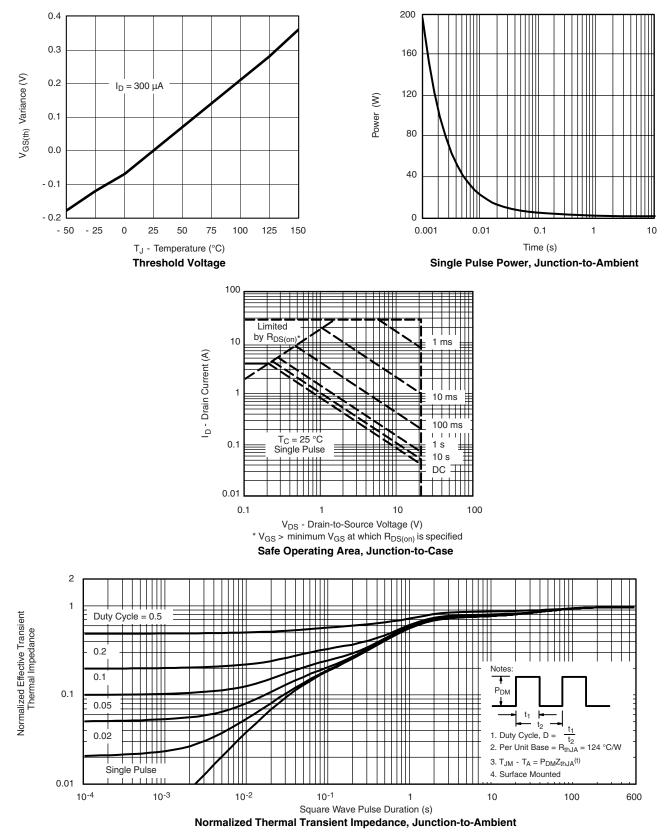
1.4

1.6

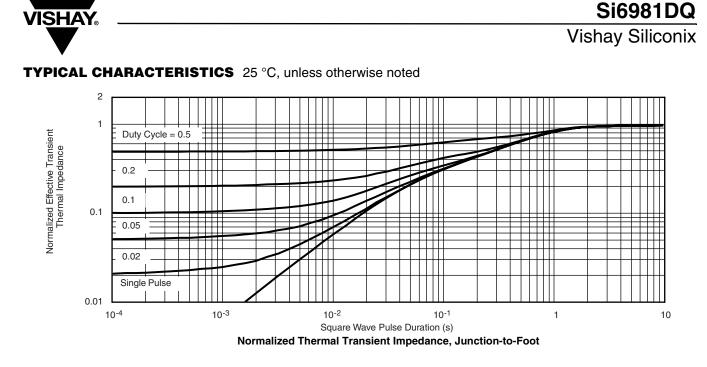
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72226.



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